

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $R_{DS(ON)}$ and to ensure minimal power loss and heat dissipation.

FEATURES

- Low $R_{DS(on)}$ provides higher efficiency and extends battery life.
- Low thermal impedance copper leadframe SOP-8 saves board space.
- Fast switching speed.
- High performance trench technology.

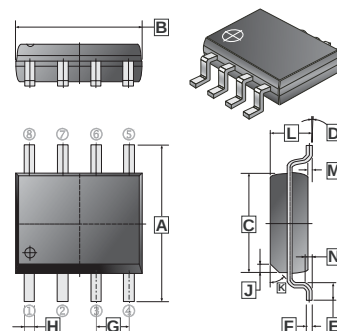
APPLICATION

DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones

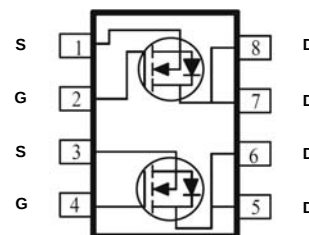
PACKAGE INFORMATION

Package	MPQ	Leader Size
SOP-8	2.5K	13 inch

SOP-8



REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	5.80	6.20	H	0.35	0.49
B	4.80	5.00	J	0.375	REF.
C	3.80	4.00	K	45°	
D	0°	8°	L	1.35	1.75
E	0.40	0.90	M	0.10	0.25
F	0.19	0.25	N	0.25	REF.
G	1.27	TYP.			



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current ²	I_{DM}	50	A
Continuous Source Current (Diode Conduction) ¹	I_S	3.1	A
Power Dissipation ¹	P_D	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Operating Junction & Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ\text{C}$
Thermal Resistance Rating			
Maximum Junction to Ambient ¹	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	$^\circ\text{C} / \text{W}$
	Steady State		$^\circ\text{C} / \text{W}$

Notes:

- 1 Surface Mounted on 1" x 1" FR4 Board.
- 2 Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

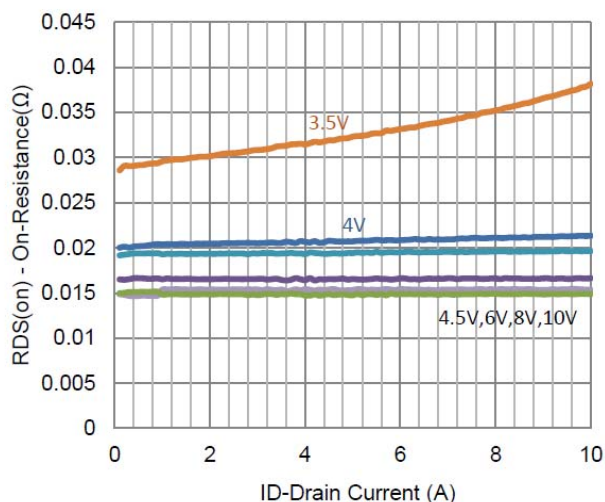
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	1	-	-	V	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$
Gate-Body Leakage	I_{GSS}	-	-	± 100	nA	$V_{DS}=0$, $V_{GS}=\pm 20\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	$V_{DS}=32\text{V}$, $V_{GS}=0$
		-	-	25	μA	$V_{DS}=32\text{V}$, $V_{GS}=0$, $T_J=55^\circ\text{C}$
On-State Drain Current ¹	$I_{D(on)}$	15	-	-	A	$V_{DS}=5\text{V}$, $V_{GS}=10\text{V}$
Drain-Source On-Resistance ¹	$R_{DS(ON)}$	-	-	23	m Ω	$V_{GS}=10\text{V}$, $I_D=6.6\text{A}$
		-	-	30		$V_{GS}=4.5\text{V}$, $I_D=5.6\text{A}$
Forward Transconductance ¹	g_{fs}	-	15	-	S	$V_{DS}=15\text{V}$, $I_D=6.6\text{A}$
Diode Forward Voltage	V_{SD}	-	0.74	-	V	$I_S=1.6\text{A}$, $V_{GS}=0$
Gate Resistance	R_g		1.4		Ω	$f=1.0\text{MHz}$
Dynamic ²						
Input Capacitance	C_{iss}		1389		pF	$V_{DS}=15\text{V}$, $V_{GS}=0$, $f=1\text{MHz}$
Output Capacitance	C_{oss}		169			
Reverse Transfer Capacitance	C_{rss}		134			
Total Gate Charge	Q_g	-	13	-	nC	$I_D=6.6\text{A}$ $V_{DS}=20\text{V}$ $V_{GS}=4.5\text{V}$
Gate-Source Charge	Q_{gs}	-	3.4	-		
Gate-Drain Charge	Q_{gd}	-	7	-		
Turn-On Delay Time	$T_{d(on)}$	-	8	-	nS	$V_{DS}=20\text{V}$ $I_D=6.6\text{A}$ $V_{GEN}=10\text{V}$ $R_L=3.1\Omega$ $R_{GEN}=6\Omega$
Rise Time	T_r	-	10	-		
Turn-Off Delay Time	$T_{d(off)}$	-	37	-		
Fall Time	T_f	-	16	-		

Notes:

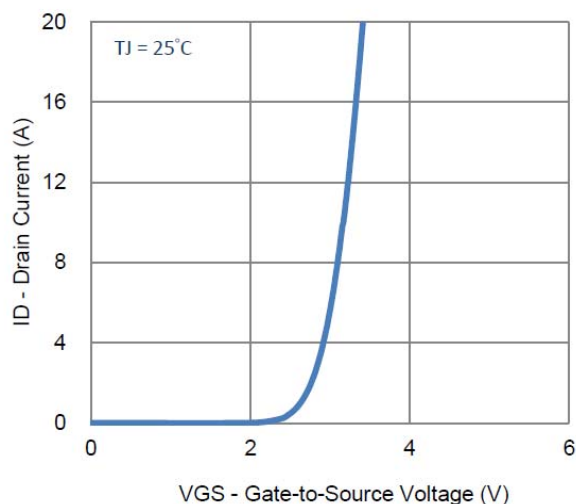
1 Pulse test : $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.

2 Guaranteed by design, not subject to production testing.

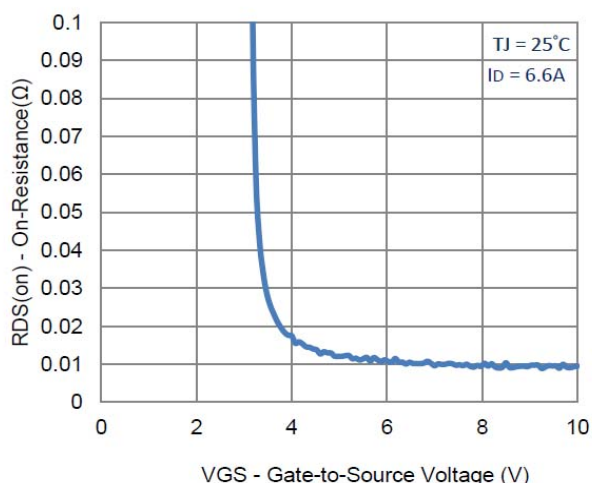
CHARACTERISTIC CURVES



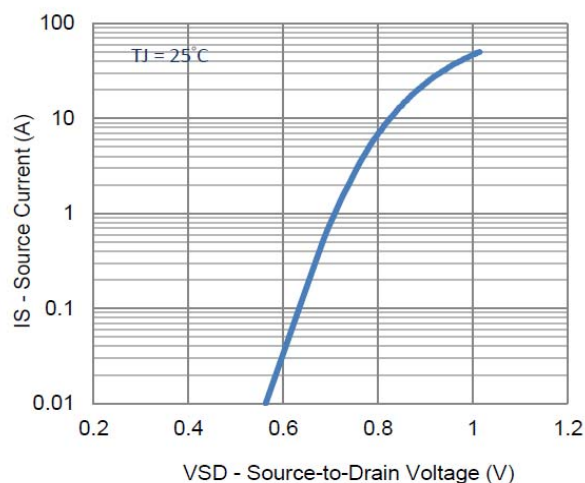
1. On-Resistance vs. Drain Current



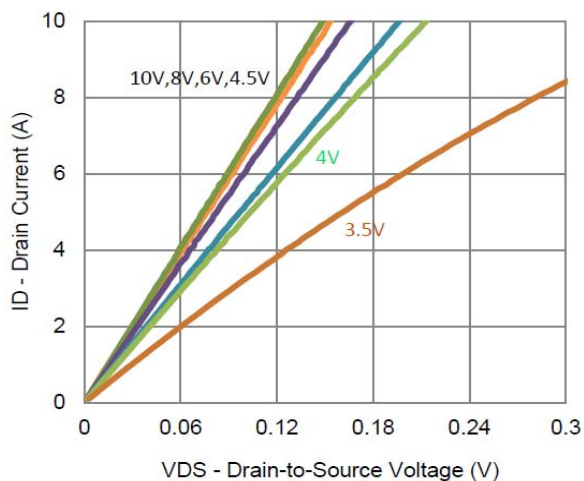
2. Transfer Characteristics



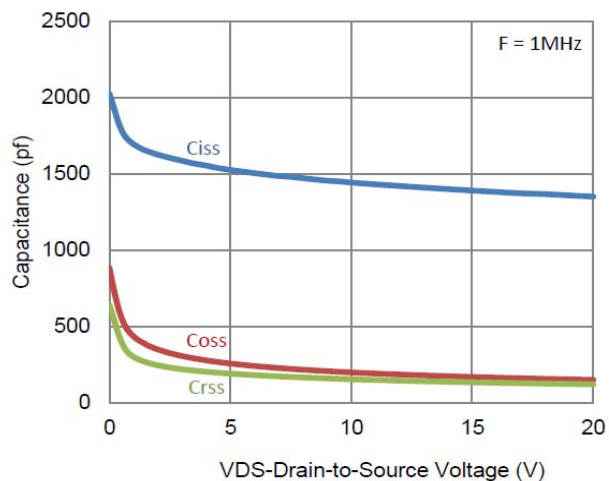
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics



6. Capacitance

CHARACTERISTIC CURVES

